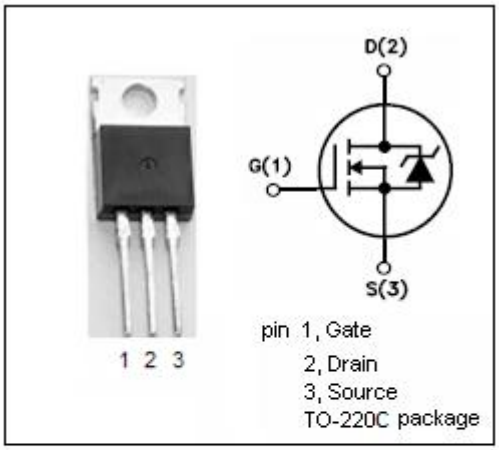
Isc N-Channel MOSFET Transistor STP100N8F6

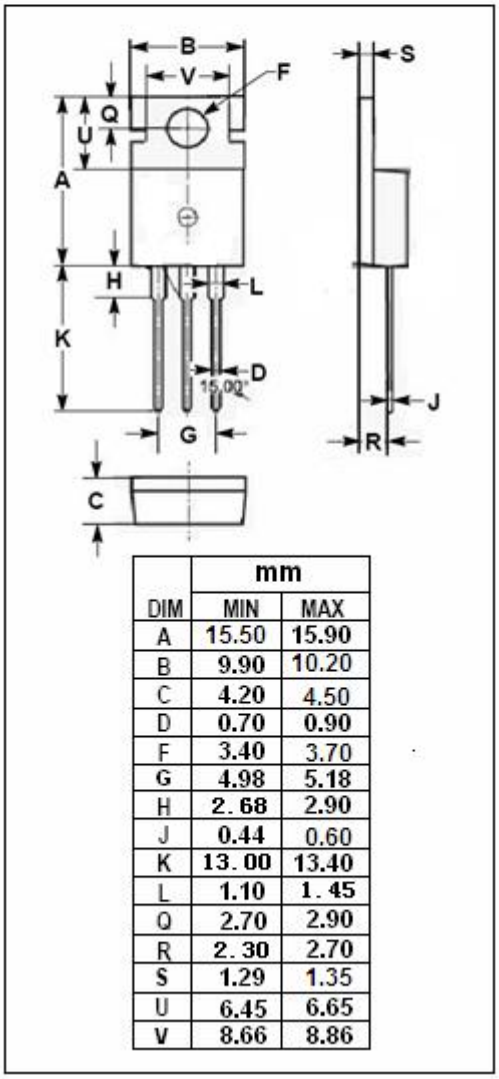


• FEATURES

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

- Switching applications



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.10	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

• ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	80	V
V_{GSS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous@T_C=25℃ T_C=100℃	100 70	A
I_{DM}	Drain Current-Single Pulsed	400	A
P_D	Total Dissipation	176	W
T_j	Operating Junction Temperature	-55~175	℃
T_{stg}	Storage Temperature	-55~175	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.85	℃/W
Rth(ch-a)	Channel-to-ambient thermal resistance	62.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 0.25mA	80			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=±20V; I_D=0.25mA	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D=50A		8	9	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 80V; V_{GS}= 0V; T_J=25℃ T_J=125℃			1 100	μA
V_{SDF}	Diode forward voltage	I_{SD}=100A, V_{GS} = 0 V			1.2	V